

### Description

The IRLML6346TRPBF uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})},$  low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

### **General Features**

V<sub>DS</sub> = 30V I<sub>D</sub> =5A

 $R_{DS(ON)}$  < 42m $\Omega$  @ V<sub>GS</sub>=10V

### Application

Battery protection

Load switch Uninterruptible power supply

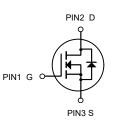
#### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRLML6346TRPBF	SOT-23	A29T	3000

### Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

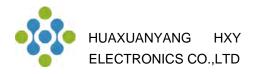
Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±12	V
١ <sub>D</sub>	Drain Current-Continuous	5	А
Ідм	Drain Current-Pulsed (Note 1)	14.4	А
PD	Maximum Power Dissipation	1	W
Тј,Тѕтб	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	125	°C <b>/W</b>





N-Channel MOSFET

N-Channel Enhancement Mode MOSFET



## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V	
Basian	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =3A	33		42	mΩ	
Rds(on)		V <sub>GS</sub> =4.5V , I <sub>D</sub> =2A		38	48	1115.2	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	0.4		1.2	V	
IDSS	Drain-Source Leakage Current	$V_{DS}$ =16V , $V_{GS}$ =0V , $T_{J}$ =25°C			1	uA	
		V <sub>DS</sub> =16V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5		
lgss	Gate-Source Leakage Current	V <sub>GS=</sub> ±12V , V <sub>DS</sub> =0V			±100	nA	
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =3A		10.5		S	
Qg	Total Gate Charge (4.5V)			4.6			
Qgs	Gate-Source Charge	V <sub>DS</sub> =15V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =3A		0.7		nC	
$Q_{gd}$	Gate-Drain Charge			1.5			
T <sub>d(on)</sub>	Turn-On Delay Time			1.6			
Tr	Rise Time	$V_{DD}$ =10V , $V_{GS}$ =4.5V , $R_{G}$ =3.3 $\Omega$		42			
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =3A		14		ns	
T <sub>f</sub>	Fall Time			7			
Ciss	Input Capacitance			310			
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		49		pF	
Crss	Reverse Transfer Capacitance			35			
ls	Continuous Source Current <sup>1,4</sup>	$V_G=V_D=0V$ , Force Current			3.6	А	
Vsd	V <sub>SD</sub> Diode Forward Voltage <sup>2</sup> V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C				1.2	V	

Note :

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width  $\,\leq\,$  300us , duty cycle  $\,\leq\,$  2%

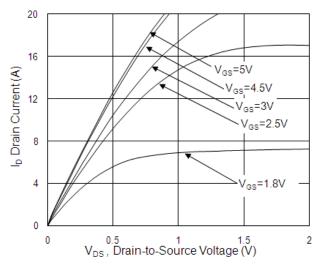
3. The power dissipation is limited by 150°C junction temperature

4. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications , should be limited by total power dissipation.



# IRLML6346TRPBF N-Channel Enhancement Mode MOSFET

### **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 

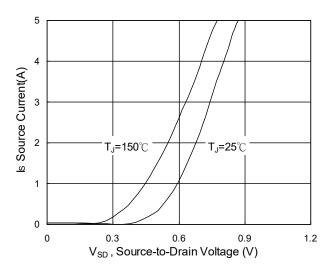


Fig.3 Forward Characteristics of Reverse

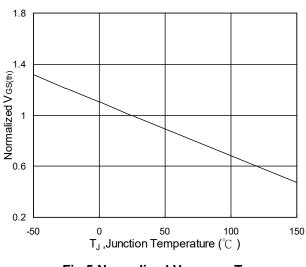


Fig.5 Normalized  $V_{GS(th)}$  vs. T<sub>J</sub>

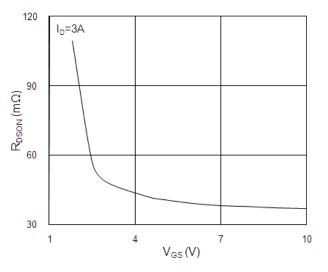


Fig.2 On-Resistance vs. Gate-Source Voltage

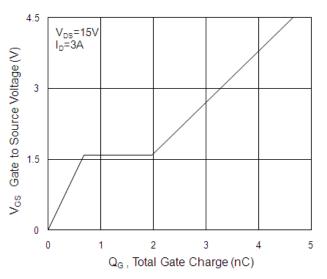


Fig.4 Gate-Charge Characteristics

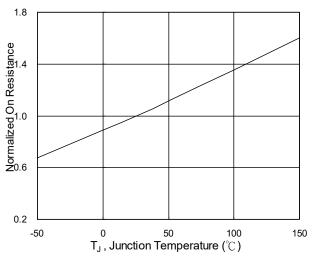
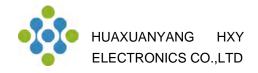


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>



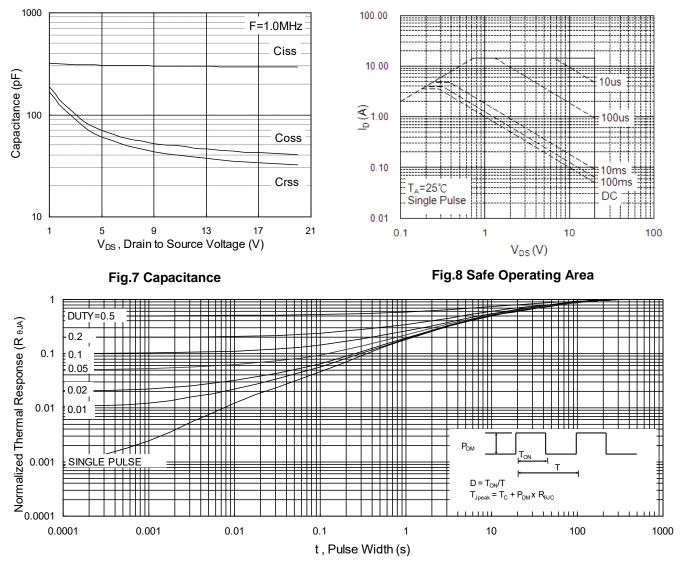


Fig.9 Normalized Maximum Transient Thermal Impedance

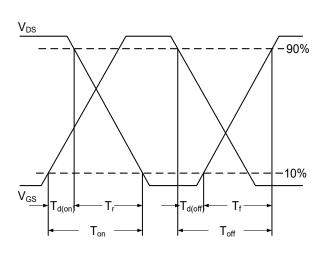
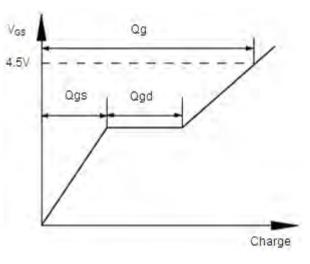


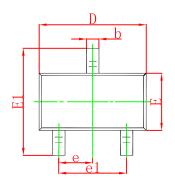
Fig.10 Switching Time Waveform

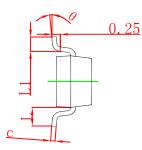


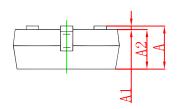




## **SOT-23 Package Outline Dimensions**

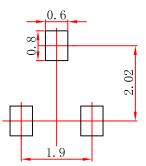






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# SOT-23 Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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